Takashi Kita

List of Publications by Year
in descending order

270 papers	3,665 citations	159573 30 h-index	182417 51 g-index
272 all docs	272 docs citations	272 times ranked	2222 citing authors

#	Article	IF	Citations
1	Intermediate band solar cells: Recent progress and future directions. Applied Physics Reviews, 2015, 2, 021302.	11.3	314
2	Increase in photocurrent by optical transitions via intermediate quantum states in direct-doped InAs/GaNAs strain-compensated quantum dot solar cell. Journal of Applied Physics, 2011, 109, .	2.5	216
3	Temperature Dependence of GaAs1-xBixBand Gap Studied by Photoreflectance Spectroscopy. Japanese Journal of Applied Physics, 2003, 42, 371-374.	1.5	184
4	Grain-size effects on dielectric phase transition of BaTiO3 ceramics. Solid State Communications, 1987, 62, 765-767.	1.9	155
5	Valence-band splitting in orderedGa0.5In0.5P studied by temperature-dependent photoluminescence polarization. Physical Review B, 1992, 45, 6637-6642.	3.2	98
6	Two-step photon up-conversion solar cells. Nature Communications, 2017, 8, 14962.	12.8	88
7	Epitaxial growth of LiNbO3â€LiTaO3thin films on Al2O3. Journal of Applied Physics, 1987, 62, 2989-2993.	2.5	82
8	Polarization-Independent Photoluminescence from Columnar InAs/GaAs Self-Assembled Quantum Dots. Japanese Journal of Applied Physics, 2002, 41, L1143-L1145.	1.5	79
9	Artificial control of optical gain polarization by stacking quantum dot layers. Applied Physics Letters, 2006, 88, 211106.	3.3	75
10	Control of optical polarization anisotropy in edge emitting luminescence of InAs/GaAs self-assembled quantum dots. Applied Physics Letters, 2004, 84, 1820-1822.	3.3	54
11	Photoreflectance characterization of surface Fermi level in asâ€grown GaAs(100). Journal of Applied Physics, 1990, 68, 5309-5313.	2.5	49
12	Optical and magnetic properties in epitaxial GdN thin films. Physical Review B, 2011, 83, .	3.2	49
13	One-dimensional miniband formation in closely stacked InAs/GaAs quantum dots. Physical Review B, 2013, 87, .	3.2	47
14	Raman and xâ€ray scattering from ultrafine semiconductor particles. Journal of Applied Physics, 1987, 61, 969-971.	2.5	45
15	Experimental and atomistic theoretical study of degree of polarization from multilayer InAs/GaAs quantum dot stacks. Physical Review B, 2011, 84, .	3.2	45
16	Zone-Folding Effects on Phonons in GaAs-AlAs Superlattices. Japanese Journal of Applied Physics, 1985, 24, 1331-1334.	1.5	43
17	Effects of absorption coefficients and intermediate-band filling in InAs/GaAs quantum dot solar cells. Applied Physics Letters, 2010, 97, .	3.3	43
18	Photoluminescence characteristics of quantum dots with electronic states interconnected along growth direction. Journal of Applied Physics, 2008, 103, .	2.5	42

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19	Electron tomography of embedded semiconductor quantum dot. Applied Physics Letters, 2008, 92, .	3.3	42
20	Transient photoconductivity responses in amorphous In-Ga-Zn-O films. Journal of Applied Physics, 2012, 112, 053715.	2.5	42
21	Raman study of GaAsâ€InxAl1â^'xAs strainedâ€layer superlattices. Journal of Applied Physics, 1985, 58, 4342-4345.	2.5	40
22	Electroreflectance polarization study of valenceâ€band states in ordered Ga0.5In0.5P. Applied Physics Letters, 1993, 63, 512-514.	3.3	39
23	Vertical-geometry all-optical switches based on InAs/GaAs quantum dots in a cavity. Applied Physics Letters, 2009, 95, 021109.	3.3	39
24	Multidirectional Observation of Photoluminescence Polarization Anisotropy in Closely Stacked InAs/GaAs Quantum Dots. Applied Physics Express, 2011, 4, 062001.	2.4	39
25	Photoreflectance characterization of built-in potential in MBE-produced As-grown GaAs surface. , 1990, , .		37
26	Bound exciton states of isoelectronic centers in GaAs:N grown by an atomically controlled doping technique. Physical Review B, 2006, 74, .	3.2	35
27	Two-step photon absorption in InAs/GaAs quantum-dot superlattice solar cells. Physical Review B, 2015, 91, .	3.2	35
28	Polarization control of electroluminescence from vertically stacked InAs/GaAs quantum dots. Applied Physics Letters, 2010, 96, .	3.3	33
29	Dynamic process of anti-Stokes photoluminescence at a long-range-orderedGa0.5In0.5P/GaAsheterointerface. Physical Review B, 1999, 59, 15358-15362.	3.2	31
30	Impurity doping in self-assembled InAs/GaAs quantum dots by selection of growth steps. Journal of Applied Physics, 2010, 108, .	2.5	31
31	Effect of internal electric field on InAs/GaAs quantum dot solar cells. Journal of Applied Physics, 2014, 115, 083510.	2.5	31
32	Suppression of thermal carrier escape and efficient photo-carrier generation by two-step photon absorption in InAs quantum dot intermediate-band solar cells using a dot-in-well structure. Journal of Applied Physics, 2014, 116, .	2.5	31
33	Carrier dynamics of the intermediate state in InAs/GaAs quantum dots coupled in a photonic cavity under two-photon excitation. Physical Review B, 2012, 86, .	3.2	30
34	Photoreflectance study on residual strain in heteroepitaxial gallium arsenide on silicon. Physical Review B, 1990, 41, 2936-2943.	3.2	29
35	Optical reflectance study of the wetting layers in (In, Ga)As self-assembled quantum dot growth on GaAs(001). Physical Review B, 2002, 66, .	3.2	27
36	Suppression of nonradiative recombination process in directly Si-doped InAs/GaAs quantum dots. Journal of Applied Physics, 2011, 110, 103511.	2.5	25

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37	Intraband carrier dynamics in InAs/GaAs quantum dots stimulated by bound-to-continuum excitation. Journal of Applied Physics, 2013, 113, .	2.5	25
38	Broadband control of emission wavelength of InAs/GaAs quantum dots by GaAs capping temperature. Journal of Applied Physics, 2015, 118, .	2.5	24
39	Effect of spacer layer thickness on multi-stacked InGaAs quantum dots grown on GaAs (311)B substrate for application to intermediate band solar cells. Journal of Applied Physics, 2012, 111, 074305.	2.5	23
40	Saturable Two-Step Photocurrent Generation in Intermediate-Band Solar Cells Including InAs Quantum Dots Embedded in Al_{0.3}Ga_{0.7}/GaAs Quantum Wells. IEEE Journal of Photovoltaics, 2016, 6, 465-472.	2.5	23
41	Deepâ€•level characterization ofnâ€•type GaAs by photoreflectance spectroscopy. Journal of Applied Physics, 1991, 69, 3691-3695.	2.5	22
42	Temperature-dependent carrier tunneling for self-assembled InAs/GaAs quantum dots with a GaAsN quantum well injector. Applied Physics Letters, 2010, 96, 151104.	3.3	22
43	Study on spin-splitting phenomena in the band structure of GdN. Applied Physics Letters, 2012, 100, .	3.3	22
44	A New Method of Photothermal Displacement Measurement by Laser Interferometric Probe -Its Mechanism and Applications to Evaluation of Lattice Damage in Semiconductors. Japanese Journal of Applied Physics, 1992, 31, 3575-3583.	1.5	21
45	The optical processes in AlInP/GaInP/AlInP quantum wells. Journal of Applied Physics, 1996, 80, 4592-4598.	2.5	21
46	High-Brightness Electron Emission from Flexible Carbon Nanotube/Elastomer Nanocomposite Sheets. Japanese Journal of Applied Physics, 2006, 45, L1186-L1189.	1.5	21
47	Preparation of composition-controlled silicon oxynitride films by sputtering; deposition mechanism, and optical and surface properties. Applied Physics A: Solids and Surfaces, 1989, 49, 305-311.	1.4	20
48	Direct optical transitions in indirect-gap (Al0.5Ga0.5)0.51In0.49P by atomic ordering. Physical Review B, 1996, 53, 15713-15718.	3.2	20
49	Photoluminescence from metastable states in long-range ordered (Al0.5Ga0.5)0.51In0.49P. Physical Review B, 1997, 55, 4411-4416.	3.2	20
50	Real time analysis of self-assembled InAs/GaAs quantum dot growth by probing reflection high-energy electron diffraction chevron image. Journal of Applied Physics, 2008, 104, 074305.	2.5	20
51	Fine structure splitting of isoelectronic bound excitons in nitrogen-doped GaAs. Physical Review B, 2008, 77, .	3.2	20
52	Observation of phase shifts in a vertical cavity quantum dot switch. Applied Physics Letters, 2011, 98, 231101.	3.3	20
53	Nanosecond-scale hot-carrier cooling dynamics in one-dimensional quantum dot superlattices. Physical Review B, 2016, 93, .	3.2	19
54	Infrared photodetector sensitized by InAs quantum dots embedded near an Al0.3Ga0.7As/GaAs heterointerface. Scientific Reports, 2020, 10, 11628.	3.3	19

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55	Carbon Nanotube/Aluminum Composites As a Novel Field Electron Emitter. Japanese Journal of Applied Physics, 2006, 45, L650-L653.	1.5	18
56	Long-wavelength emission from nitridized InAs quantum dots. Applied Physics Letters, 2003, 83, 4152-4153.	3.3	17
57	Anisotropic magneto-optical effects in one-dimensional diluted magnetic semiconductors. Physical Review B, 2006, 74, .	3.2	17
58	Hot-carrier solar cells using low-dimensional quantum structures. Applied Physics Letters, 2014, 105, 171904.	3.3	17
59	Efficient two-step photocarrier generation in bias-controlled InAs/GaAs quantum dot superlattice intermediate-band solar cells. Scientific Reports, 2017, 7, 5865.	3.3	17
60	Photocurrent polarization in longâ€range ordered Ga0.5In0.5P. Applied Physics Letters, 1995, 66, 1794-1796.	3.3	16
61	Extended wavelength emission to 1.3Î¼m in nitrided InAsâˆ•GaAs self-assembled quantum dots. Journal of Applied Physics, 2005, 97, 024306.	2.5	15
62	Side electron emission device using carbon nanofiber/elastomer composite sheet. Applied Physics Letters, 2008, 92, .	3.3	15
63	Narrow-band deep-ultraviolet light emitting device using Al1âˆ'xGdxN. Applied Physics Letters, 2008, 93, .	3.3	15
64	Analysis of thermoreflectance signals and characterization of thermal conductivity of metal thin films. Review of Scientific Instruments, 2009, 80, 124901.	1.3	15
65	Polarization-insensitive optical gain characteristics of highly stacked InAs/GaAs quantum dots. Journal of Applied Physics, 2014, 115, .	2.5	15
66	Epitaxial two-dimensional nitrogen atomic sheet in GaAs. Applied Physics Letters, 2014, 104, .	3.3	15
67	Increasing conversion efficiency of two-step photon up-conversion solar cell with a voltage booster hetero-interface. Scientific Reports, 2018, 8, 872.	3.3	15
68	Detailed Design and Characterization of All-Optical Switches Based on InAs/GaAs Quantum Dots in a Vertical Cavity. IEEE Journal of Quantum Electronics, 2010, 46, 1582-1589.	1.9	14
69	Broadband light sources using InAs quantum dots with InGaAs strain-reducing layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 331-333.	0.8	14
70	Multidirectional observation of an embedded quantum dot. Applied Physics Letters, 2007, 90, 041911.	3.3	13
71	Temperature dependence of photoluminescence characteristics of excitons in stacked quantum dots and quantum dot chains. Journal of Applied Physics, 2010, 107, 073506.	2.5	13
72	Carrier Time-of-Flight Measurement Using a Probe Structure for Direct Evaluation of Carrier Transport in Multiple Quantum Well Solar Cells. IEEE Journal of Photovoltaics, 2014, 4, 1518-1525.	2.5	13

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73	Microscopic observation of carrier-transport dynamics in quantum-structure solar cells using a time-of-flight technique. Applied Physics Letters, 2015, 107, .	3.3	13
74	Hot-carrier generation and extraction in InAs/GaAs quantum dot superlattice solar cells. Semiconductor Science and Technology, 2019, 34, 094003.	2.0	13
75	Carrier localization effects in energy up conversion at ordered (Al0.5Ga0.5)0.5In0.5P/GaAs heterointerface. Journal of Applied Physics, 1998, 84, 359-363.	2.5	12
76	Dual chopped photoreflectance spectroscopy for nondestructive characterization of semiconductors and semiconductor nanostructures. Review of Scientific Instruments, 2008, 79, 046110.	1.3	12
77	Intermediate band photovoltaics based on interbandâ€"intraband transitions using In_{0.53}Ga_{0.47}As/InP superlattice. Progress in Photovoltaics: Research and Applications, 2013, 21, 472-480.	8.1	12
78	Observation of quantum beat oscillations and ultrafast relaxation of excitons confined in GaAs thin films by controlling probe laser pulses. Journal of Applied Physics, 2012, 111, 023505.	2.5	12
79	Thermal annealing effects on ultra-violet luminescence properties of Gd doped AlN. Journal of Applied Physics, 2015, 117, 163105.	2.5	12
80	Comparison of Electron and Hole Mobilities in Multiple-Quantum-Well Solar Cells Using a Time-of-Flight Technique. IEEE Journal of Photovoltaics, 2015, 5, 1613-1620.	2.5	12
81	Adiabatic two-step photoexcitation effects in intermediate-band solar cells with quantum dot-in-well structure. Scientific Reports, 2019, 9, 7859.	3.3	12
82	Anisotropic magneto-optical effects in(CdTe)0.5(Cd0.75Mn0.25Te)0.5tilted superlattices. Physical Review B, 2004, 69, .	3.2	11
83	Optical Polarization Properties of InAs/GaAs Quantum Dot Semiconductor Optical Amplifier. Japanese Journal of Applied Physics, 2005, 44, 2528-2530.	1.5	11
84	Ferromagnetic properties of GdN thin films studied by temperature dependent circular polarized spectroscopy. Applied Physics Letters, 2012, 101, 072403.	3.3	11
85	Graphoepitaxial growth of ZnS on a textured natural crystalline surface relief foreign substrate. Journal of Applied Physics, 1988, 64, 3492-3496.	2.5	10
86	Bright electron emission from Si-doped AlN thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2490-2493.	0.8	10
87	Narrowband ultraviolet field-emission device using Gd-doped AlN. IOP Conference Series: Materials Science and Engineering, 2009, 1, 012001.	0.6	10
88	Extremely uniform bound exciton states in nitrogen Î´-doped GaAs studied by photoluminescence spectroscopy in external magnetic fields. Journal of Applied Physics, 2011, 110, 083522.	2.5	10
89	Energy Conversion Efficiency of Solar Cells. Green Energy and Technology, 2019, , .	0.6	10
90	Analysis of lattice defects induced by ion implantation with photoâ€acoustic displacement measurements. Journal of Applied Physics, 1994, 76, 5681-5689.	2.5	9

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91	Polarization controlled edge emission from columnar InAs/GaAs self-assembled quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1137-1140.	0.8	9
92	Tuning optical and ferromagnetic properties of thin GdN films by nitrogen-vacancy centers. European Physical Journal B, 2013, 86, 1.	1.5	9
93	Giant optical splitting in the spin-states assisting a sharp magnetic switching in GdN thin films. Applied Physics Letters, 2013, 102, .	3.3	9
94	Electronic transitions in GdN band structure. Journal of Applied Physics, 2014, 115, .	2.5	9
95	Optical properties of tilted II-VI superlattices grown on vicinal surfaces. Physical Review B, 2001, 63, .	3.2	8
96	Multi-stacked InAs/GaNAs quantum dots with direct Si doping for use in intermediate band solar cell. , 2010, , .		8
97	Effect of exciton oscillator strength on upconversion photoluminescence in GaAs/AlAs multiple quantum wells. Applied Physics Letters, 2014, 105, .	3.3	8
98	Two-step photocurrent generation enhanced by miniband formation in InAs/GaAs quantum dot superlattice intermediate-band solar cells. Applied Physics Letters, 2017, 110, .	3.3	8
99	Spatially resolved electronic structure of an isovalent nitrogen center in GaAs. Physical Review B, 2017, 96, .	3.2	8
100	Reply to: â€œThermal artefacts in two-photon solar cell experimentsâ€• Nature Communications, 2019, 10, 956.	12.8	8
101	Resonant exciton excitation photoluminescence and dynamics in a GaAs/AlAs multiple quantum well with internal electric field. AIP Advances, 2020, 10, .	1.3	8
102	Graphoepitaxial growth of germanium by laser recrystallization. Journal of Applied Physics, 1989, 66, 4770-4774.	2.5	7
103	Self-assembled growth of InAs-quantum dots and postgrowth behavior studied by reflectance-difference spectroscopy. Applied Surface Science, 2000, 159-160, 503-507.	6.1	7
104	Atomically controlled doping of nitrogen on GaAs(001) surfaces. Journal of Crystal Growth, 2007, 301-302, 34-37.	1.5	7
105	Photoluminescence dynamics of coupled quantum dots. Journal of Luminescence, 2008, 128, 975-977.	3.1	7
106	Flexible Field Emission Device Using Carbon Nanofiber Nanocomposite Sheet. Applied Physics Express, 0, 1, 074004.	2.4	7
107	Thermal Conductivity Measurement Technique for Cu-Pt Alloy Thin Films by a Modulated Thermoreflectance Method. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 2009, 73, 434-438.	0.4	7
108	Bound biexciton luminescence in nitrogen <i>Î´</i>â€•doped GaAs. Physica Status Solidi (B): Basic Research, 2011, 248, 464-467.	1.5	7

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109	Optical and ferromagnetic properties of GdN thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 488-490.	0.8	7
110	Influence of local atomic configuration in AlGdN phosphor thin films on deep ultra-violet luminescence intensity. Journal of Applied Physics, 2011, 110, 093108.	2.5	7
111	Photocarrier transport dynamics in InAs/GaAs quantum dot superlattice solar cells using time-of-flight spectroscopy. Physical Review B, 2016, 94, .	3.2	7
112	Improving laser cooling efficiencies of Yb-doped yttrium aluminum garnet by utilizing non-resonant anti-Stokes emission at high temperatures. Optics Express, 2019, 27, 34961.	3.4	7
113	Solid phase recrystallization in molecular beam deposited gallium arsenide. Applied Physics Letters, 1989, 54, 706-708.	3.3	6
114	Graphoepitaxial growth of germanium on the textured natural crystalline surface relief duplicated on a foreign substrate. Journal of Applied Physics, 1989, 65, 4730-4734.	2.5	6
115	Resonant coupling between confined and unconfined states in a finite-periodIn0.24Ga0.76As/GaAs strained-layer superlattice. Physical Review B, 1994, 50, 2420-2424.	3.2	6
116	Photocurrent anisotropy in compositional modulated superlattice of long-range ordered Ga0.5In0.5P. Journal of Electronic Materials, 1996, 25, 661-665.	2.2	6
117	Spin polarization of exciton luminescence from orderedGa0.5In0.5P. Physical Review B, 1998, 57, R15044-R15047.	3.2	6
118	Dynamic process of two-dimensional InAs growth in Stranskiâ€“Krastanov mode. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 891-895.	2.7	6
119	Ultrafast All-Optical Control of Excitons Confined in GaAs Thin Films. Applied Physics Express, 0, 1, 112401.	2.4	6
120	Vertically stacked InAs quantum dots for polarization-independent semiconductor optical amplifiers. Proceedings of SPIE, 2010, , .	0.8	6
121	Control of stacking direction and optical anisotropy in InAs/GaAs quantum dots by In flux. Journal of Applied Physics, 2013, 114, .	2.5	6
122	Control of optical properties in cyanine dye thin film fabricated by a layer-by-layer method. Journal of Applied Physics, 2014, 115, 083503.	2.5	6
123	Emission-wavelength tuning of InAs quantum dots grown on nitrogen-Î´-doped GaAs(001). Journal of Applied Physics, 2016, 119, 194306.	2.5	6
124	Wide Frequency Tuning of Continuous Terahertz Wave Generated by Difference Frequency Mixing under Exciton-Excitation Conditions in a <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Ga</mml:mi><mml:mi>As</mml:mi></mml:math> / <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Al</mml:mi><mml:mi>As</mml:mi></mml:math> Multiple Quantum Well. P	3.8	6
125	Polarization-insensitive fiber-to-fiber gain of semiconductor optical amplifier using closely stacked InAs/GaAs quantum dots. Japanese Journal of Applied Physics, 2020, 59, 032002.	1.5	6
126	Anomaly of dielectric properties in tensâ€nanometerâ€thick lead lanthanum zirconate titanate films on a platinum substrate. Journal of Applied Physics, 1989, 66, 3924-3926.	2.5	5

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127	Electron-Beam Electroreflectance Spectroscopy of Semiconductors. Japanese Journal of Applied Physics, 1996, 35, 5367-5373.	1.5	5
128	Magnetophotoluminescence study of theGa0.5In0.5P/GaAsheterointerface with a ordering-induced two-dimensional electron gas. Physical Review B, 2002, 66, .	3.2	5
129	Fourier transformed photoreflectance characterization of interface electric fields in GaAs/GaInP heterojunction bipolar transistor wafers. Journal of Applied Physics, 2003, 94, 6487-6490.	2.5	5
130	Transition with a hysteresis cycle in surface reconstruction on GaAs(001) observed by optical reflectance spectroscopy. Physical Review B, 2003, 67, .	3.2	5
131	Vertical stacking of InAs quantum dots for polarization-insensitive semiconductor optical amplifiers. Journal of Physics: Conference Series, 2010, 245, 012076.	0.4	5
132	Spatially Resolved Thermal Conductivity of Intermetallic Compounds Measured by Micro-Thermoreflectance Method. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 2010, 74, 740-745.	0.4	5
133	Saturation of FÃ¶rster resonance energy transfer between two optically nonlinear cyanine dyes of small Stokes shift energies in polymer thin films. Journal of Applied Physics, 2011, 110, 083521.	2.5	5
134	Energy band structure and the halfâ€filling of the intermediate band in the quantumâ€dot solar cell. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 622-624.	0.8	5
135	Field-emission properties of carbon nanotube composite in side-electron emission configuration. Journal of Applied Physics, 2011, 109, 074307.	2.5	5
136	Pulse modulation towards low-power operation based on the quantum beat of excitons in a GaAs/AlAs multiple quantum well. Journal Physics D: Applied Physics, 2014, 47, 105101.	2.8	5
137	Effects of non-exciton components excited by broadband pulses on quantum beats in a GaAs/AlAs multiple quantum well. Scientific Reports, 2017, 7, 41496.	3.3	5
138	Hot-carrier generation in a solar cell containing InAs/GaAs quantum-dot superlattices as a light absorber. Applied Physics Express, 2018, 11, 082303.	2.4	5
139	Wide-wavelength-range control of photoluminescence polarization in closely stacked InAs/GaAs quantum dots. Journal of Applied Physics, 2019, 125, .	2.5	5
140	Two-step excitation induced photovoltaic properties in an InAs quantum dot-in-well intermediate-band solar cell. Journal of Applied Physics, 2021, 129, .	2.5	5
141	Higher-interband electroreflectance of long-range orderedGa0.5In0.5P. Physical Review B, 1996, 54, 16714-16718.	3.2	4
142	Time-resolved observation of anti-Stokes photoluminescence at ordered Ga0.5In0.5P and GaAs interfaces. Journal of Luminescence, 2000, 87-89, 269-271.	3.1	4
143	Strain effects on photoluminescence polarization of InAs/GaAs self-assembled quantum dots. Physica Status Solidi (B): Basic Research, 2003, 238, 229-232.	1.5	4
144	Effects of indium segregation on optical properties of nitrogen-doped InAs/GaAs quantum dots. Journal of Applied Physics, 2008, 104, 103532.	2.5	4

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145	Side electron emission device using a composite of carbon nanofibers and aluminum. Thin Solid Films, 2009, 518, 530-533.	1.8	4
146	Intraband relaxation process in highly stacked quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 46-49.	0.8	4
147	Dynamics of above-barrier state excitons in multi-stacked quantum dots. Journal of Applied Physics, 2011, 110, 093515.	2.5	4
148	Multiple excitation process in deep-ultraviolet emission from AlGdN thin films pumped by an electron beam. Journal of Applied Physics, 2012, 111, 083526.	2.5	4
149	Rapid dephasing related to intersubband transitions induced by exciton quantum beats observed by a pump-probe technique in a GaAs/AlAs multiple quantum well. Physical Review B, 2015, 91, .	3.2	4
150	Fabrication of cyanine dye thin films grown by a layer-by-layer method. Materials Research Express, 2015, 2, 076402.	1.6	4
151	Microscopic properties of degradation-free capped GdN thin films studied by electron spin resonance. Journal of Applied Physics, 2015, 117, 043909.	2.5	4
152	Effects of rapid thermal annealing on two-dimensional delocalized electronic states of the epitaxial N Î´-doped layer in GaAs. Applied Physics Letters, 2016, 108, 111905.	3.3	4
153	Effective drift mobility approximation in multiple quantum-well solar cell. , 2016, , .		4
154	Two-step photocurrent generation enhanced by the fundamental-state miniband formation in intermediate-band solar cells using a highly homogeneous InAs/GaAs quantum-dot superlattice. Applied Physics Express, 2018, 11, 012301.	2.4	4
155	Reciprocal Relation Between Intraband Carrier Generation and Interband Recombination at the Heterointerface of Two-Step Photon Up-Conversion Solar Cells. Physical Review Applied, 2020, 14, .	3.8	4
156	Increase in terahertz-wave generation by difference frequency mixing by the overlap of exciton states in different GaAs/AlAs quantum wells and spectroscopic measurements. Optics Express, 2021, 29, 24387.	3.4	4
157	Photoluminescence and Photoreflectance Study of Electronic Structure in Pseudomorphic n-AlGaAs/InGaAs/GaAs. Japanese Journal of Applied Physics, 1992, 31, L756-L758.	1.5	3
158	Excitonic states inCdTe/Cd0.74Mg0.26Tequantum wires grown on vicinal substrates. Physical Review B, 2003, 67, .	3.2	3
159	Anisotropic exchange interaction caused by hole-spin reorientation in (CdTe)0.5(Cd0.75Mn0.25Te)0.5 tilted superlattices grown on Cd0.74Mg0.26Te(001) vicinal surface. Journal of Crystal Growth, 2005, 275, e2221-e2224.	1.5	3
160	Emission-wavelength extension of nitrided InAs/GaAs quantum dots with different sizes. Journal of Crystal Growth, 2007, 301-302, 709-712.	1.5	3
161	Anisotropic magneto-optical effects inCdTe/Cd0.75Mn0.25Tequantum wire structures. Physical Review B, 2008, 78, .	3.2	3
162	Transient reflectivity response with negative time delay caused by femtosecond pulse propagation in GaAs thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S139-S142.	0.8	3

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163	Propagation velocity of excitonic polaritons confined in GaAs thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 378-380.	0.8	3
164	Depolarization effect on optical control of exciton states confined in GaAs thin films. Journal of Applied Physics, 2011, 110, 043514.	2.5	3
165	Dephasing of Excitonic Polaritons Confined in GaAs Thin Films. Journal of the Physical Society of Japan, 2011, 80, 034704.	1.6	3
166	Magneto-optical effect in GdN epitaxial thin film. Journal of Physics: Conference Series, 2013, 417, 012053.	0.4	3
167	Effects of exciton line widths on the amplitude of quantum beat oscillations. Applied Physics Express, 2016, 9, 062801.	2.4	3
168	Increase in exciton decay rate due to plane-to-plane interaction between cyanine thin films. AIP Advances, 2016, 6, 075209.	1.3	3
169	Polarization characteristics of electroluminescence and net modal gain in highly stacked InAs/GaAs quantum-dot laser devices. Journal of Applied Physics, 2016, 120, .	2.5	3
170	Effect of lattice-mismatch strain on electron dynamics in InAs/GaAs quantum dots as seen by time-domain terahertz spectroscopy. Journal Physics D: Applied Physics, 2018, 51, 305102.	2.8	3
171	Determination of silicon wafer site flatness using dual heterodyne interferometers with sub-nanometer precision. Review of Scientific Instruments, 2020, 91, 065114.	1.3	3
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